

isc Silicon NPN Power Transistor

2SC4746

DESCRIPTION

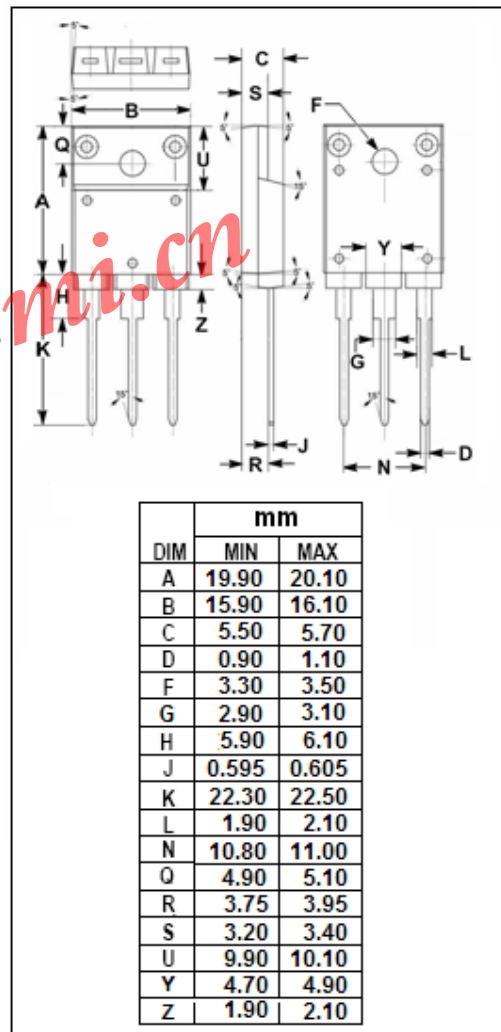
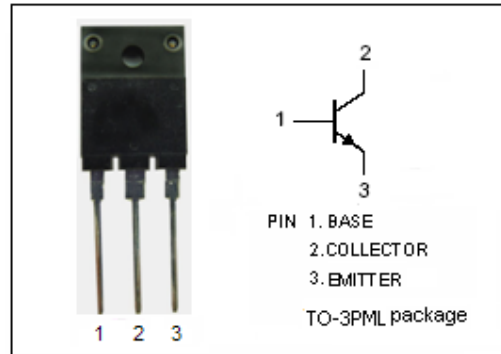
- High Breakdown Voltage-  
:  $V_{CBO}=1500V$  (Min)
- High Switching Speed

APPLICATIONS

- Designed for character display horizontal deflection output stage applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current- Continuous	8	A
$I_{C(surge)}$	Collector Current-Surge	20	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



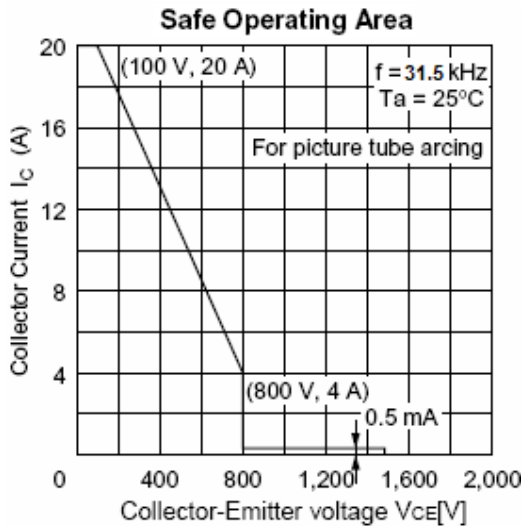
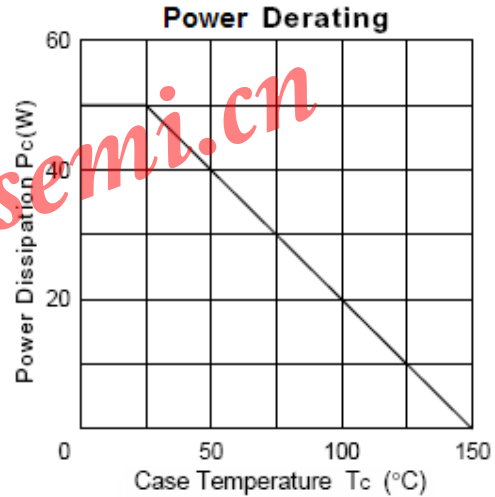
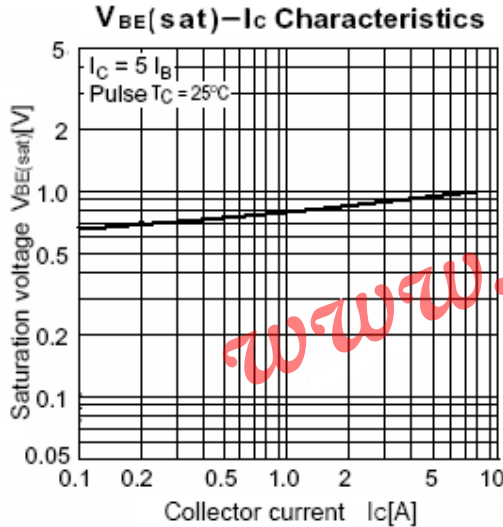
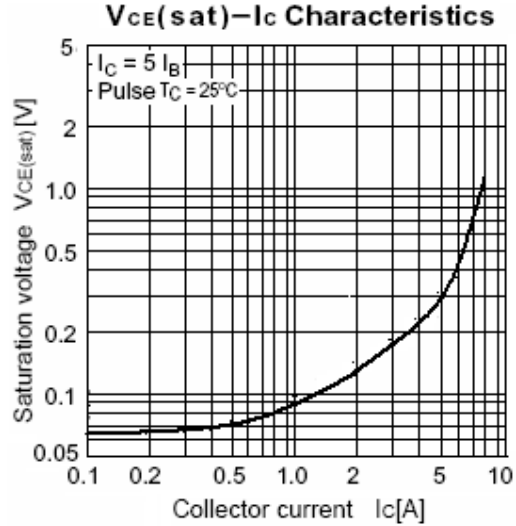
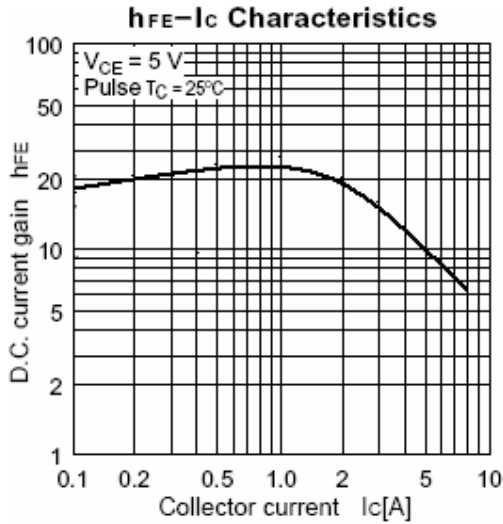
**isc Silicon NPN Power Transistor****2SC4746****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}$ ; $R_{BE}=\infty$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}$ ; $I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=7\text{A}$ ; $I_B=1.4\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=7\text{A}$ ; $I_B=1.4\text{A}$			1.5	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=1500\text{V}$ ; $R_{BE}=0$			500	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=1\text{A}$ ; $V_{CE}=5\text{V}$	8		38	
$t_f$	Fall Time	$I_{CP}=7\text{A}$ ; $I_{B1}=1.4\text{A}$			0.5	$\mu\text{s}$

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